

L Number	Hits	Search Text	DB	Time stamp
1	820	silver near4 (indium near2 tin near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:23
2	228	((silver near4 (indium near2 tin near2 oxide)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:23
3	5	((silver near4 (indium near2 tin near2 oxide)) and semiconductor) and (leadframe (lead adj frame))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:17
4	205	((silver near4 (indium near2 tin near2 oxide)) and semiconductor) and (optical light window)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:23
5	160	((silver near4 (indium near2 tin near2 oxide)) and semiconductor) and (optical light window)) and (pattern lead trace)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:23
6	80	((silver near4 (indium near2 tin near2 oxide)) and semiconductor) and (optical light window)) and (pattern lead trace)) and (chip die (integrated adj circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:23
7	231	(silver near4 (indium near2 tin near2 oxide)) with layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:23
8	84	((silver near4 (indium near2 tin near2 oxide)) with layer) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:23
9	79	((silver near4 (indium near2 tin near2 oxide)) with layer) and semiconductor) and (optical light window)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:23
10	57	((silver near4 (indium near2 tin near2 oxide)) with layer) and semiconductor) and (optical light window)) and (pattern lead trace)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:23
11	24	((silver near4 (indium near2 tin near2 oxide)) with layer) and semiconductor) and (optical light window)) and (pattern lead trace)) and (chip die (integrated adj circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/12 15:24